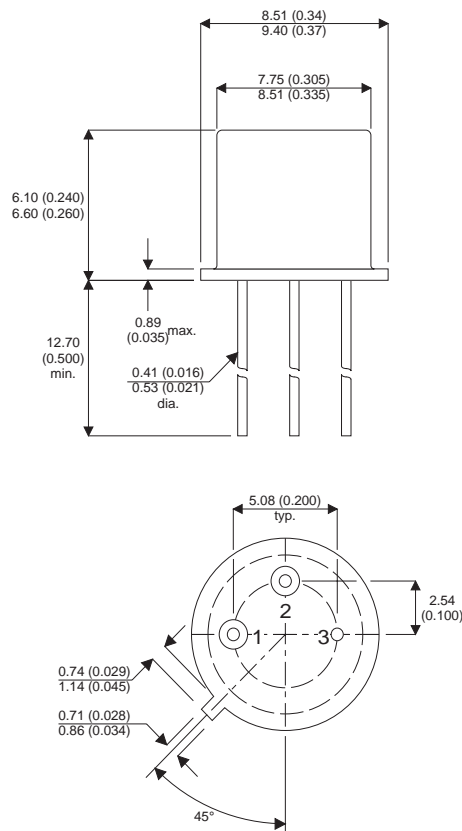


MECHANICAL DATA

Dimensions in mm (inches)



TO-39 (TO-205AD) PACKAGE

PIN 1 – Emitter PIN 2 – Base PIN 3 – Collector

SILICON EPITAXIAL NPN TRANSISTOR

FEATURES

General purpose power transistor for switching and linear applications in a hermetic TO-39 package.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage		500V
V_{CER}	Collector – Emitter Voltage	$R = 10\Omega$	500V
V_{EBO}	Emitter – Base Reverse Voltage		5V
I_C	Continuous Collector Current		0.5A
P_{TOT}	Total Device Dissipation	$T_C = 25^\circ\text{C}$	2W
T_J, T_{STG}	Maximum Storage and Junction Temperature Range		200°C
$R_{\theta JC}$	Thermal Impedance Junction To Case		50°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Base Leakage Current			0.006	mA
h_{FE}	D.C Current Gain			180	—
f_t	Transition Frequency		20		MHz

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.